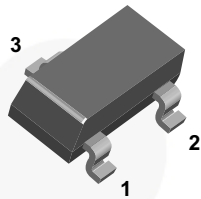


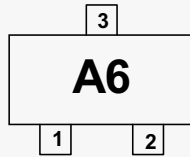


February 2015

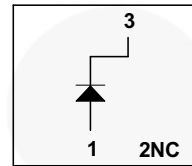
BAS16 Small Signal Diode



SOT-23



Connection Diagram



Ordering Information

Part Number	Top Mark	Package	Packing Method
BAS16	A6	SOT-23 3L	Tape and Reel, 7 inch Reel, 3000 pcs
BAS16_D87Z	A6	SOT-23 3L	Tape and Reel, 13 inch Reel, 10000 pcs

Absolute Maximum Ratings^{(1), (2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage	85	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current	Pulse Width = 1.0 second	1.0
		Pulse Width = 1.0 microsecond	2.0
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$

Notes:

1. These ratings are based on a maximum junction temperature of 150°C .
2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C}/\text{W}$

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V_R	Breakdown Voltage	$I_R = 5.0 \mu\text{A}$	85		V
V_F	Forward Voltage	$I_F = 1.0 \text{ mA}$		715	mV
		$I_F = 10 \text{ mA}$		855	mV
		$I_F = 50 \text{ mA}$		1.0	V
		$I_F = 150 \text{ mA}$		1.25	V
I_R	Reverse Current	$V_R = 75 \text{ V}$		1.0	μA
		$V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$		30	
		$V_R = 75 \text{ V}, T_A = 150^\circ\text{C}$		50	
C_T	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		2.0	pF
t_{rr}	Reverse Recovery Time	$I_F = I_R = 10 \text{ mA}, I_{RR} = 1.0 \text{ mA}, R_L = 100 \Omega$		6.0	ns

Typical Performance Characteristics

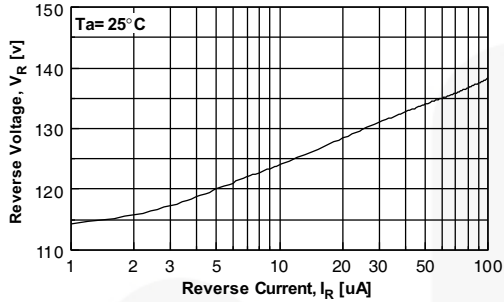
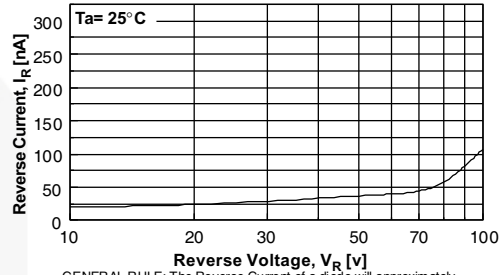


Figure 1. Reverse Voltage vs. Reverse Current
 V_R - 1.0 to 100 μA



GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

Figure 2. Reverse Current vs. Reverse Voltage
 I_R - 10 to 100 V

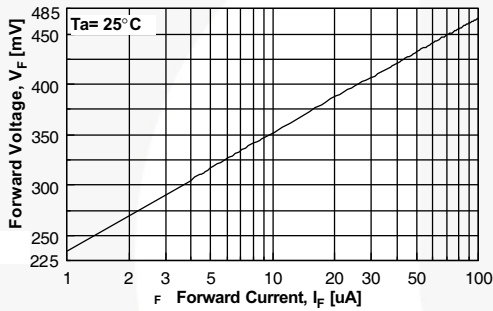


Figure 3. Forward Voltage vs. Forward Current
 V_F - 1.0 to 100 μA

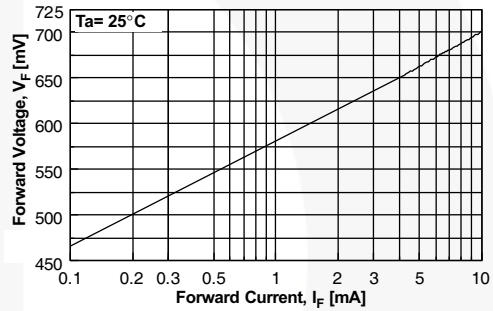


Figure 4. Forward Voltage vs. Forward Current
 V_F - 1.0 to 100 mA

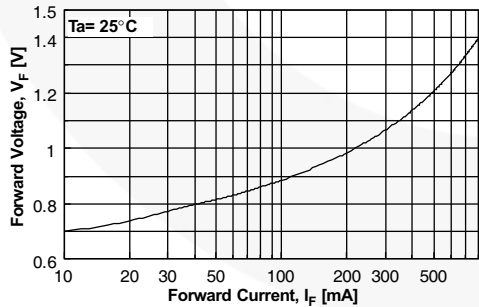


Figure 5. Forward Voltage vs. Forward Current
 V_F - 10 to 800 mA

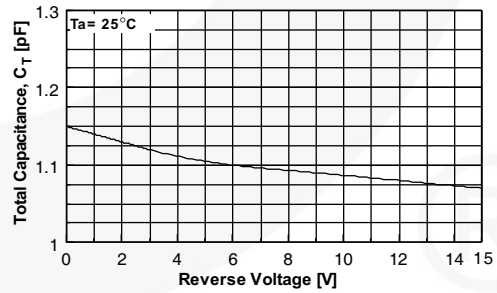


Figure 6. Total Capacitance

Typical Performance Characteristics (Continued)

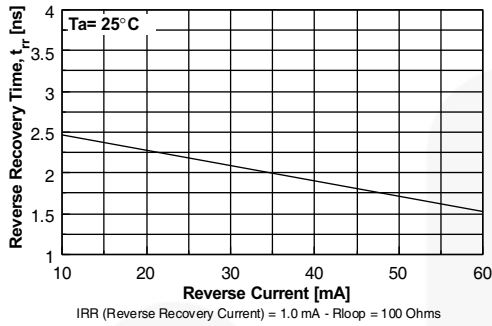


Figure 7. Reverse Recovery Time vs. Reverse Current

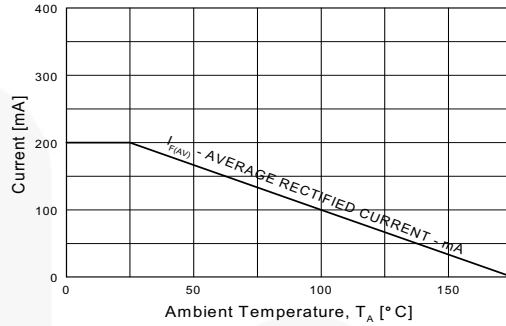


Figure 8. Average Rectified Current ($I_{F(AV)}$) vs. Ambient Temperature (T_A)

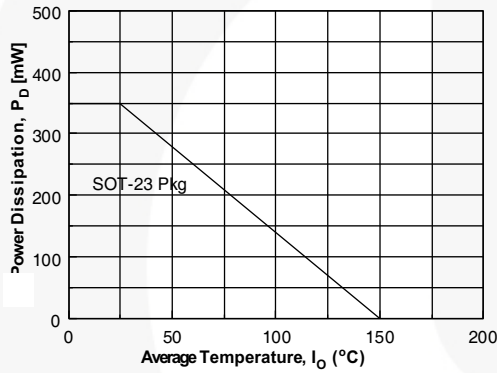


Figure 9. Power Derating Curve

Physical Dimensions

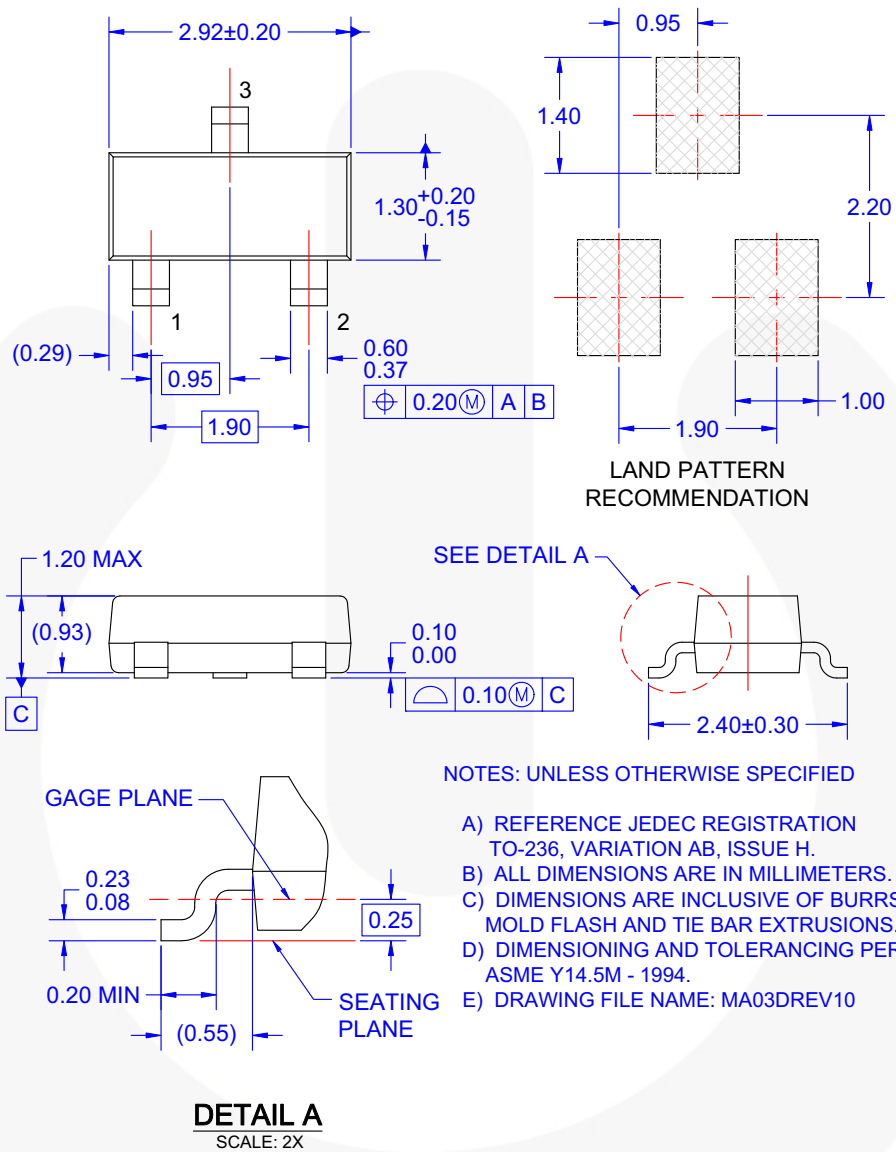


Figure 10. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE